

### 1N4148WS, 1N4448WS, 1N914BWS

- ◇ General purpose diodes
- ◇ Fast switching devices
- ◇ **SOD323F Thin SMD package (Fig-1)**
- ◇ RoHS compliant / Green EMC
- ◇ Matte Tin (Sn) Lead finish
- ◇ Moisture Level Sensitivity 1
- ◇ Cathode Band / Device marking

Device Marking Code	
<b>1N4148WS</b>	<b>S1</b>
<b>1N4448WS</b>	<b>S2</b>
<b>1N914BWS</b>	<b>S3</b>

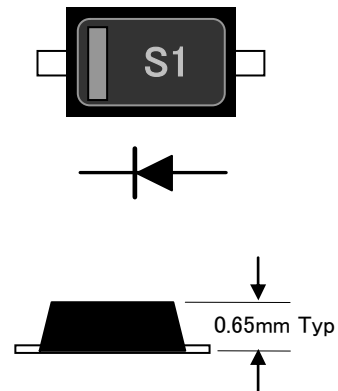


Fig.-1 Package. height

#### Absolute Maximum Ratings (Ta = 25 °C)

Symbol	Parameter	Value	Units
$V_{RSM}$	Non-Repetitive Peak Reverse Voltage	100	V
$V_{RRM}$	Repetitive Peak Reverse Voltage	75	V
$I_{FRM}$	Repetitive Peak Forward Current	300	mA
$I_{FSM}$	Non-Repetitive Peak Forward Current *1	2	A
$I_o$	Continuous Forward Current	150	mA
$P_D$	Power Dissipation	200	mW
$T_J$	Junction Temperature	150	°C
$T_{STG}$	Storage Temperature	-55 to +150	°C

\*1 Pulse width = 1  $\mu$  s

#### Electrical Characteristics (Ta = 25 °C)

Symbol	Parameter	Conditions	Min	Max	Units
$BV_R$	Breakdown Voltage	$I_R = 100 \mu A$	100		V
		$I_R = 5 \mu A$	75		V
$I_R$	Reverse Current	$V_R = 20V$		25	nA
		$V_R = 75V$		5	$\mu A$
$V_F$	Forward Voltage	$I_F = 5mA$ *2	0.62	0.72	V
		$I_F = 10mA$		1	V
		$I_F = 100mA$ *2		1	V
C	Capacitance	$V_R = 0V, f = 1MHz$		4	pF
$T_{RR}$	Reverse Recovery Time	$I_F = 10mA, V_R = 6V$ $I_{RR} = 1mA, R_L = 100 \Omega$		4	ns

\*2 Excluded 1N4148WS

### Package Dimensions

